



#### N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BV <sub>DSS</sub>	RDS(ON) Max	I <sub>D</sub> T <sub>A</sub> = +25°C
30V	60mΩ @ V <sub>GS</sub> = 10V	4A
307	$70m\Omega$ @ $V_{GS} = 4.5V$	3A

### **Description**

This MOSFET has been designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### **Applications**

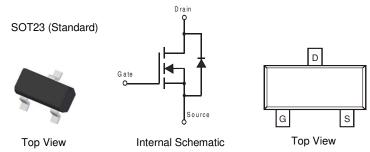
- Backlighting
- Power Management Functions
- DC-DC Converters
- Motor Control

#### **Features**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <a href="https://www.diodes.com/quality/product-definitions/">https://www.diodes.com/quality/product-definitions/</a>

#### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (3)
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)



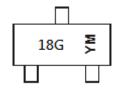
# Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMG3418L-7	Standard	SOT23 (Standard)	3000/Tape & Reel
DMG3418L-13	Standard	SOT23 (Standard)	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**



18G = Product Type Marking Code YM or  $\overline{Y}M$  = Date Code Marking Y or  $\overline{Y}$  = Year (ex: I = 2021) M = Month (ex: 9 = September)

Date Code Key

Date Code Rey												
Year	2013		2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	Α			J	K	L	М	N	0	Р	R	S
				_		_			_			•
	1				I		I	I		-		
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



# **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

Charact	eristic	Symbol	Value	Unit
Drain Source Voltage		V <sub>DSS</sub>	30	V
Gate-Source Voltage		Vgss	±12	V
Drain Current (Note 5)	$T_A = +25$ °C $T_A = +70$ °C	ID	4.0 3.1	А
Drain Current (Note 6)	Pulsed	I <sub>DM</sub>	15	Α

# **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5) $T_{A} = +25^{\circ}C$ $T_{A} = +70^{\circ}C$	·   Pn	1.4 0.9	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	Reja	90	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

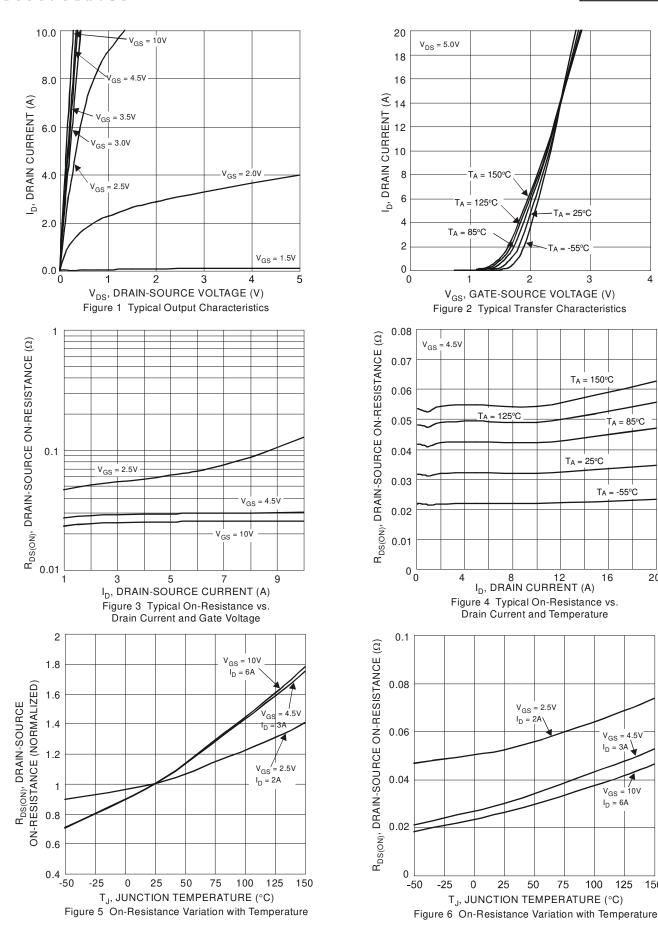
### **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)				<u> </u>		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	_	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$
Zero Gate Voltage Drain Current	IDSS	_	_	1	μΑ	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
Gate-Body Leakage	lgss	_	_	±100	nA	$V_{GS} = \pm 12V$ , $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.5	_	1.5	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$
		_	25	60		$V_{GS} = 10V$ , $I_D = 4A$
Static Drain-Source On-Resistance	RDS(ON)	_	30	70	mΩ	$V_{GS} = 4.5V, I_{D} = 3A$
		_	50	150		$V_{GS} = 2.5V, I_{D} = 2A$
Source-Drain Diode Forward Voltage	V <sub>SD</sub>	_	_	1.2	V	Vgs = 0V, Is = 2.0A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	_	464.3		pF	
Output Capacitance	Coss	_	49.5	_	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V - f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	43.8	_	pF	1 = 1.000112
Total Gate Charge	Qg	_	5.5	_		
Gate-Source Charge	Q <sub>gs</sub>	_	1.1	_	nC	$V_{GS} = 4.5V, V_{DS} = 15V,$ $I_{D} = 4A$
Gate-Drain Charge	Qgd	_	1.8	_		ID = 4A
Turn-On Delay Time	t <sub>D(ON)</sub>	_	1.9	_	ns	
Turn-On Rise Time	t <sub>R</sub>	_	1.6	_	ns	V <sub>DD</sub> = 15V, V <sub>GEN</sub> = 10V,
Turn-Off Delay Time	tD(OFF)	_	10.3	_	ns	RGEN = $3\Omega$ , R <sub>L</sub> = $3.75\Omega$
Turn-Off Fall Time	tF	_	2.0	_	ns	

Notes:

- 5. Device mounted on FR-4 PCB with 2oz. copper and test pulse width t ≤ 10s.
  6. Repetitive rating, pulse width limited by junction temperature.
  7. Short duration pulse test used to minimize self-heating effect.
  8. Guaranteed by design. Not subject to product testing.





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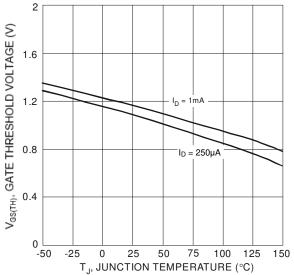
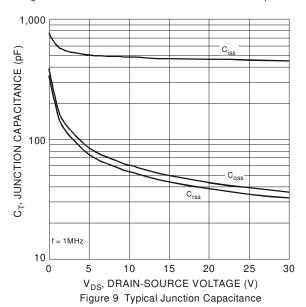
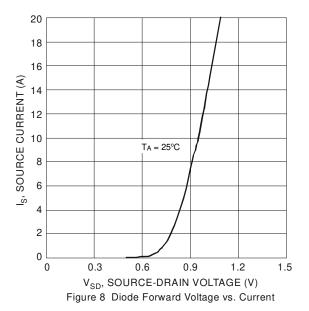


Figure 7 Gate Threshold Variation vs. Junction Temperature





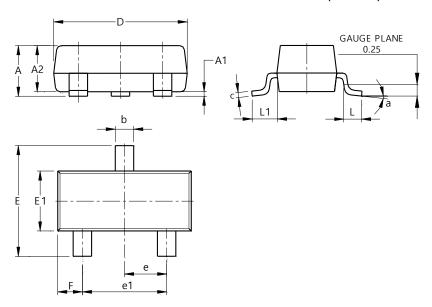
10 (X) 8 V<sub>DS</sub> = 15V I<sub>D</sub> = 4A (X) I<sub>D</sub> = 4A



# Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23 (Standard)

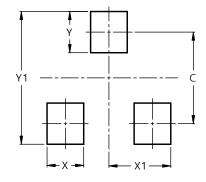


SOT23 (Standard)						
Dim	Min	Max	Тур			
Α	0.90	1.15	1.025			
A1	0.00	0.10	0.05			
A2	0.85	1.10	0.975			
b	0.30	0.51	0.40			
С	0.080	0.202	0.11			
D	2.80	3.00	2.90			
Е	2.25	2.55	2.40			
E1	1.20	1.40	1.30			
е	0.89	1.03	0.915			
e1	1.78	2.05	1.83			
F	0.40	0.60	0.535			
L1	0.45	0.61	0.55			
L	0.25	0.55	0.40			
а	0°	8°				
All Dimensions in mm						

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23 (Standard)



Dimensions	Value (in mm)		
С	2.0		
Х	0.8		
X1	1.35		
Υ	0.9		
Y1	2.9		



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